

100-Tap Digitally Programmable Potentiometer (DPP™)



FEATURES

- 100-position linear taper potentiometer
- Non-volatile EEPROM wiper storage
- 10nA ultra-low standby current
- Single supply operation: 2.5V 6.0V
- Increment up/down serial interface
- Resistance values: 1kΩ, 10kΩ, 50kΩ and 100kΩ
- Available in PDIP, SOIC, TSSOP and MSOP packages

APPLICATIONS

- Automated product calibration
- Remote control adjustments
- Offset, gain and zero control
- Tamper-proof calibrations
- Contrast, brightness and volume controls
- Motor controls and feedback systems
- Programmable analog functions

For Ordering Information details, see page 12.

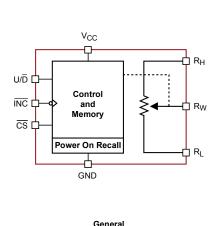
DESCRIPTION

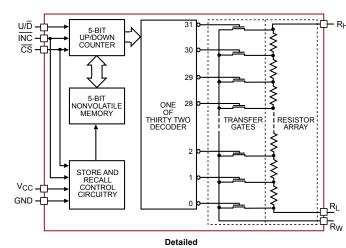
The CAT5113 is a single digitally programmable potentiometer (DPP™) designed as a electronic replacement for mechanical potentiometers. Ideal for automated adjustments on high volume production lines, they are also well suited for applications where equipment requiring periodic adjustment is either difficult to access or located in a hazardous or remote environment.

The CAT5113 contains a 100-tap series resistor array connected between two terminals R_H and R_L . An up/down counter and decoder that are controlled by three input pins, determines which tap is connected to the wiper, R_W . The wiper setting, stored in nonvolatile memory, is not lost when the device is powered down and is automatically reinstated when power is returned. The wiper can be adjusted to test new system values without affecting the stored setting. Wiper-control of the CAT5113 is accomplished with three input control pins, \overline{CS} , U/\overline{D} , and \overline{INC} . The \overline{INC} input increments the wiper in the direction which is determined by the logic state of the U/\overline{D} input. The \overline{CS} input is used to select the device and also store the wiper position prior to power down.

The digitally programmable potentiometer can be used as a three-terminal resistive divider or as a two-terminal variable resistor.

FUNCTIONAL DIAGRAM





Electronic Potentiometer Implementation



PIN CONFIGURATION

PDIP 8-Lead (L) SOIC 8 Lead (V) MSOP 8 Lead (Z)

1	8	V_{CC}
2	7	cs
3	6	R_{L}
4	5	R_{WB}
	2	2 7 3 6

TSSOP 8 Lead (Y)

$\overline{\text{cs}}$	1	8	R_{L}
$V_{\text{CC}} \\$	2	7	R_{WB}
ĪNC	3	6	GND
U/D	4	5	R_{H}

PIN DESCRIPTION

INC: Increment Control Input

The $\overline{\text{INC}}$ input moves the wiper in the up or down direction determined by the condition of the U/ $\overline{\text{D}}$ input.

U/D: Up/Down Control Input

The U/ \overline{D} input controls the direction of the wiper movement. When in a high state and \overline{CS} is low, any high-to-low transition on \overline{INC} will cause the wiper to move one increment toward the R_H terminal. When in a low state and \overline{CS} is low, any high-to-low transition on \overline{INC} will cause the wiper to move one increment towards the R_L terminal.

R_H: High End Potentiometer Terminal

 R_{H} is the high end terminal of the potentiometer. It is not required that this terminal be connected to a potential greater than the R_{L} terminal. Voltage applied to the R_{H} terminal cannot exceed the supply voltage, V_{CC} or go below ground, GND.

Rw: Wiper Potentiometer Terminal

 R_W is the wiper terminal of the potentiometer. Its position on the resistor array is controlled by the control inputs, $\overline{INC},\,U/\overline{D}$ and $\overline{CS}.$ Voltage applied to the R_W terminal cannot exceed the supply voltage, V_{CC} or go below ground, GND.

R_L: Low End Potentiometer Terminal

 R_{L} is the low end terminal of the potentiometer. It is not required that this terminal be connected to a potential less than the R_{H} terminal. Voltage applied to the R_{L} terminal cannot exceed the supply voltage, V_{CC} or go below ground, GND. R_{L} and R_{H} are electrically interchangeable.

CS: Chip Select

The chip select input is used to activate the control input of the CAT5113 and is active low. When in a

PIN DESCRIPTIONS

Name	Function
ĪNC	Increment Control
U/D	Up/Down Control
R _H	Potentiometer High Terminal
GND	Ground
R_W	Buffered Wiper Terminal
R _L	Potentiometer Low Terminal
C S	Chip Select
V _{CC}	Supply Voltage

high state, activity on the \overline{INC} and U/\overline{D} inputs will not affect or change the position of the wiper.

DEVICE OPERATION

The CAT5113 operates like a digitally controlled potentiometer with $R_{\rm H}$ and $R_{\rm L}$ equivalent to the high and low terminals and $R_{\rm W}$ equivalent to the mechanical potentiometer's wiper. There are 100 available tap positions including the resistor end points, $R_{\rm H}$ and $R_{\rm L}$. There are 99 resistor elements connected in series between the $R_{\rm H}$ and $R_{\rm L}$ terminals. The wiper terminal is connected to one of the 100 taps and controlled by three inputs, $\overline{\rm INC}$, U/D and $\overline{\rm CS}$. These inputs control a seven-bit up/down counter whose output is decoded to select the wiper position. The selected wiper position can be stored in non-volatile memory using the $\overline{\rm INC}$ and $\overline{\rm CS}$ inputs.

With $\overline{\text{CS}}$ set LOW the CAT5113 is selected and will respond to the U/D and $\overline{\text{INC}}$ inputs. HIGH to LOW transitions on $\overline{\text{INC}}$ wil increment or decrement the wiper (depending on the state of the U/D input and seven-bit counter). The wiper, when at either fixed terminal, acts like its mechanical equivalent and does not move beyond the last position. The value of the counter is stored in nonvolatile memory whenever $\overline{\text{CS}}$ transitions HIGH while the $\overline{\text{INC}}$ input is also HIGH. When the CAT5113 is powered-down, the last stored wiper counter position is maintained in the nonvolatile memory. When power is restored, the contents of the memory are recalled and the counter is set to the value stored.

With INC set low, the CAT5113 may be de-selected and powered down without storing the current wiper position in nonvolatile memory. This allows the system to always power up to a preset value stored in nonvolatile memory.



OPERATION MODES

ĪNC	<u>cs</u>	U/D	Operation
High to Low	Low	High	Wiper toward H
High to Low	Low	Low	Wiper toward L
High	Low to High	Х	Store Wiper Position
Low	Low to High	Х	No Store, Return to Standby
Х	High	Х	Standby

ABSOLUTE MAXIMUM RATINGS(1)

Parameters	Ratings	Units
Supply Voltage		
V _{CC} to GND	-0.5 to +7V	V
Inputs		
CS to GND	-0.5 to V _{CC} +0.5	V
INC to GND	-0.5 to V _{CC} +0.5	V
U/D to GND	-0.5 to V _{CC} +0.5	V
H to GND	-0.5 to V _{CC} +0.5	V
L to GND	-0.5 to V _{CC} +0.5	V
W to GND	-0.5 to V _{CC} +0.5	V

Parameters	Ratings	Units
Operating Ambient Temperature		
Commercial ('C' or Blank suffix)	0 to 70	°C
Industrial ('I' suffix)	-40 to +85	°C
Junction Temperature	+150	°C
Storage Temperature	-65 to 150	°C
Lead Soldering (10s max)	+300	°C

RELIABILITY CHARACTERISTICS

Symbol	Parameter	Test Method	Min	Тур	Max	Units
$V_{ZAP}^{(2)}$	ESD Susceptibility	MIL-STD-883, Test Method 3015	2000			V
I _{LTH} ^{(2) (3)}	Latch-Up	JEDEC Standard 17	100			mA
T_DR	Data Retention	MIL-STD-883, Test Method 1008	100			Years
N _{END}	Endurance	MIL-STD-883, Test Method 1003	1,000,000			Stores

DC ELECTRICAL CHARACTERISTICS

Vcc = +2.5V to +6V unless otherwise specified

Power Supply

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V_{CC}	Operating Voltage Range		2.5	_	6.0	V
1	Supply Current (Ingrament)	$V_{CC} = 6V, f = 1MHz, I_{W} = 0$	_	_	100	μA
I _{CC1}	Supply Current (Increment)	$V_{CC} = 6V, f = 250kHz, I_{W} = 0$	_	_	50	μA
1	I _{CC2} Supply Current (Write)	Programming, V _{CC} = 6V	_	_	1000	μΑ
I _{CC2}		V _{CC} = 3V	_	_	500	μA
I _{SB1} ⁽³⁾	Supply Current (Standby)	$\overline{CS} = V_{CC} - 0.3V$ U/ \overline{D} , $\overline{INC} = V_{CC} - 0.3V$ or GND	_	0.01	1	μA

- (1) Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions outside of those listed in the operational sections of this specification is not implied. Exposure to any absolute maximum rating for extended periods may affect device performance and reliability.
- (2) This parameter is tested initially and after a design or process change that affects the parameter.
- (3) Latch-up protection is provided for stresses up to 100mA on address and data pins from -1V to V_{CC} + 1V
- (4) I_W = source or sink
- (5) These parameters are periodically sampled and are not 100% tested.



Logic Inputs

Symbol	Parameter	Conditions	Min	Тур	Max	Units
I _{IH}	Input Leakage Current	$V_{IN} = V_{CC}$	_	_	10	μΑ
I _{IL}	Input Leakage Current	V _{IN} = 0V	_	-	-10	μΑ
V _{IH1}	TTL High Level Input Voltage	4.5V ≤ V _{CC} ≤ 5.5V	2	_	V _{CC}	V
V _{IL1}	TTL Low Level Input Voltage	$4.5V \leq V_{CC} \leq 5.5V$	0	_	0.8	V
V _{IH2}	CMOS High Level Input Voltage	2.5V ≤ V _{CC} ≤ 6V	V _{CC} x 0.7	_	V _{CC} + 0.3	V
V _{IL2}	CMOS Low Level Input Voltage	2.5V ≤ V _{CC} ≤ 0V	-0.3		V _{CC} x 0.2	V

Potentiometer Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Units
		-01 Device		1		
ь	Potentiometer Resistance	-10 Device		10		kΩ
R _{POT}		-50 Device		50		
		-00 Device		100		
	Pot. Resistance Tolerance				±20	%
V_{RH}	Voltage on R _H pin		0		V_{CC}	V
V_{RL}	Voltage on R _L pin		0		V _{CC}	V
	Resolution			1		%
INL	Integral Linearity Error	I _W ≤ 2μA		0.5	1	LSB
DNL	Differential Linearity Error	I _W ≤ 2μA		0.25	0.5	LSB
В	Min on Desistance	V_{CC} = 5V, I_W = 1mA			400	Ω
R_{WI}	Wiper Resistance	V _{CC} = 2.5V, I _W = 1mA			1000	Ω
I _W	Wiper Current	(1)	-4.4		4.4	mA
TC _{RPOT}	TC of Pot Resistance			300		ppm/°C
TC _{RATIO}	Ratiometric TC				20	ppm/°C
V _N	Noise	100kHz / 1kHz		8/24		nV/√Hz
C _H /C _L /C _W	Potentiometer Capacitances			8/8/25		pF
fc	Frequency Response	Passive Attenuator, 10kΩ		1.7		MHz

Note:

(1) This parameter is not 100% tested.



AC CONDITIONS OF TEST

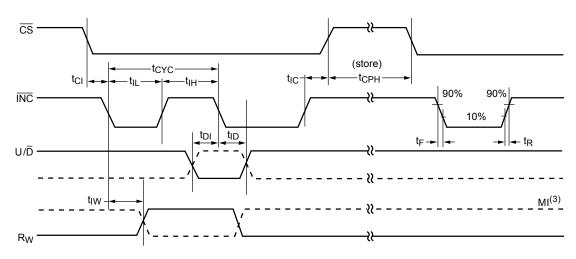
V _{CC} Range	$2.5V \le V_{CC} \le 6V$
Input Pulse Levels	$0.2V_{CC}$ to $0.7V_{CC}$
Input Rise and Fall Times	10ns
Input Reference Levels	0.5V _{CC}

AC OPERATING CHARACTERISTICS

 V_{CC} = +2.5V to +6.0V, V_{H} = V_{CC} , V_{L} = 0V, unless otherwise specified

Symbol	Parameter	Min	Typ ⁽¹⁾	Max	Units
t _{CI}	CS to INC Setup	100	_	_	ns
t_{DI}	U/D to INC Setup	50	_	_	ns
t_{ID}	U/D to INC Hold	100	_	_	ns
t_{IL}	INC LOW Period	250	_	_	ns
t_{IH}	INC HIGH Period	250	_	_	ns
t _{IC}	INC Inactive to CS Inactive	1	_	_	μs
t _{CPH}	CS Deselect Time (NO STORE)	100	_	_	ns
t _{CPH}	CS Deselect Time (STORE)	10	_	_	ms
t_{IW}	INC to V _{OUT} Change	_	1	5	μs
t_{CYC}	INC Cycle Time	1	_	_	μs
$t_R, t_F^{(2)}$	INC Input Rise and Fall Time	_	_	500	μs
t _{PU} ⁽²⁾	Power-up to Wiper Stable			1	ms
t _{WR}	Store Cycle	_	5	10	ms

A.C. TIMING



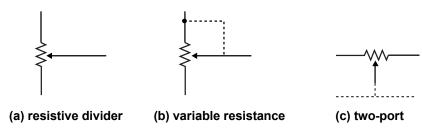
- (1) Typical values are for $T_A = 25$ °C and nominal supply voltage.
- (2) This parameter is periodically sampled and not 100% tested.
- (3) MI in the A.C. Timing diagram refers to the minimum incremental change in the W output due to a change in the wiper position.



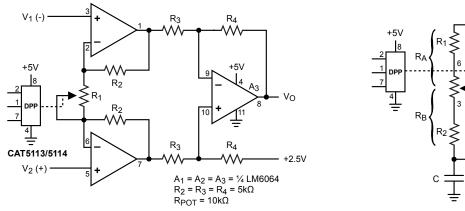
+5V

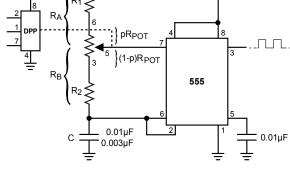
APPLICATIONS INFORMATION

Potentiometer Configuration



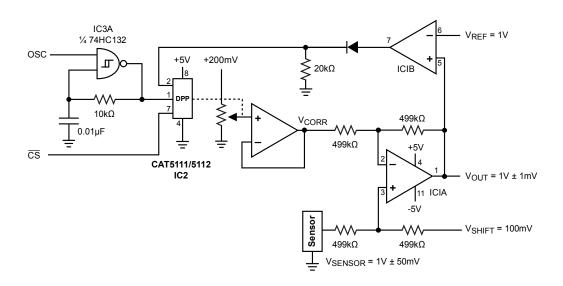
Applications





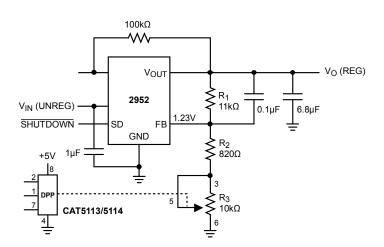
Programmable Instrumentation Amplifier

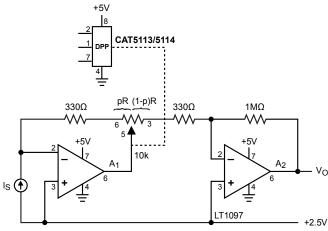
Programmable Sq. Wave Oscillator (555)



Sensor Auto Referencing Circuit

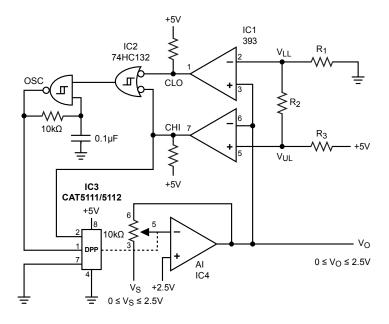


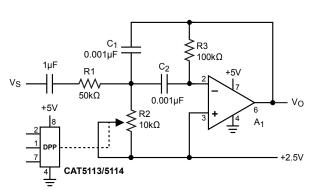




Programmable Voltage Regulator

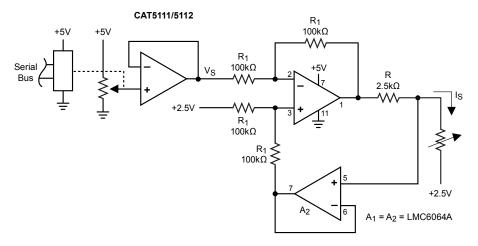
Programmable I to V Convertor





Automatic Gain Control

Programmable Bandpass Filter

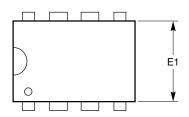


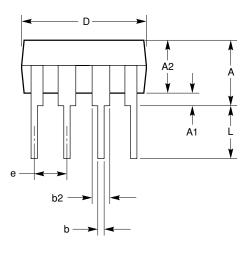
Programmable Current Source/Sink

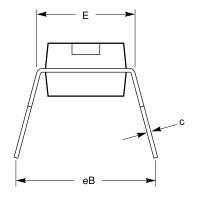


PACKAGE OUTLINES

PDIP 8-LEAD (300MIL) (L)







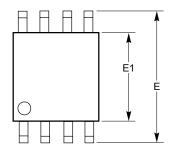
SYMBOL	MIN	NOM	MAX
Α			4.57
A1	0.38		
A2	3.05		3.81
b	0.36	0.46	0.56
b2	1.14		1.77
С	0.21	0.26	0.35
D	9.02		10.16
E	7.62	7.87	8.25
E1	6.09	6.35	7.11
е		2.54 BSC	
eB	7.87		9.65
L	2.92		3.81

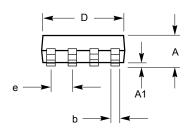
For current Tape and Reel information, download the PDF file from: http://www.catsemi.com/documents/tapeandreel.pdf.

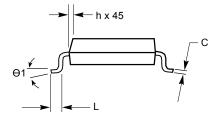
- (1) All dimensions are in millimeters.
- (2) Complies with JEDEC Standard MS001.
- (3) Dimensioning and tolerancing per ANSI Y14.5M-1982



SOIC 8-LEAD NARROW BODY (150MIL) (V)







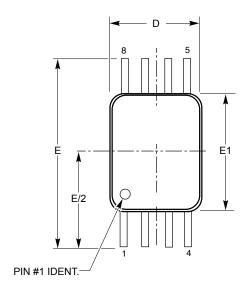
SYMBOL	MIN	NOM	MAX
A1	0.10		0.25
Α	1.35		1.75
b	0.33		0.51
С	0.19		0.25
D	4.80		5.00
E	5.80		6.20
E1	3.80		4.00
е		1.27 BSC	
h	0.25		0.50
L	0.40		1.27
Θ1	0°		8°

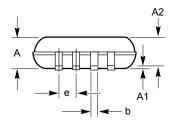
For current Tape and Reel information, download the PDF file from: http://www.catsemi.com/documents/tapeandreel.pdf.

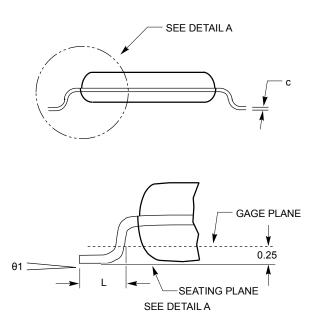
- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC Specification MS-012.



8-LEAD TSSOP (Y)







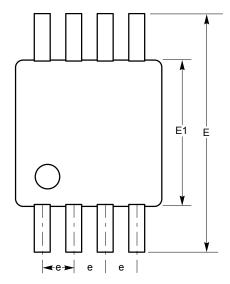
SYMBOL	MIN	NOM	MAX
Α			1.20
A1	0.05		0.15
A2	0.80	0.90	1.05
b	0.19		0.30
С	0.09		0.20
D	2.90	3.00	3.10
E	6.30	6.4	6.50
E1	4.30	4.40	4.50
е		0.65 BSC	
L	0.50	0.60	0.75
θ1	0.00		8.00

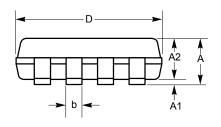
For current Tape and Reel information, download the PDF file from: http://www.catsemi.com/documents/tapeandreel.pdf.

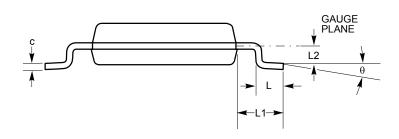
- (1) All dimensions are in millimeters.
- (2) Complies with JEDEC Standard MO-153



8-LEAD MSOP (Z)







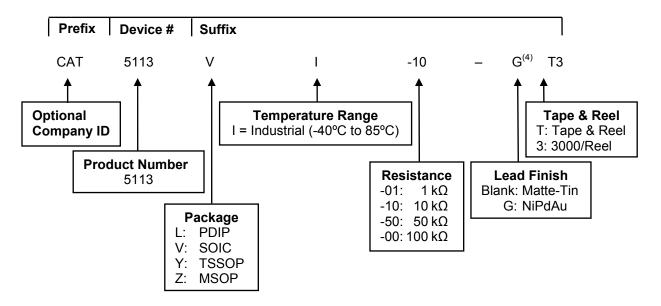
SYMBOL	MIN	NOM	MAX
Α			1.1
A1	0.05	0.10	0.15
A2	0.75	0.85	0.95
b	0.28	0.33	0.38
С			
D	2.90	3.00	3.10
Е	4.80	4.90	5.00
E1	2.90	3.00	3.10
е		0.65 BSC	
L	0.35	0.45	0.55
L1			
L2			
θ	0°		6°

For current Tape and Reel information, download the PDF file from: http://www.catsemi.com/documents/tapeandreel.pdf.

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC Specification MS-187.
- (3) Stand off height/coplanarity are considered as special characteristics.



EXAMPLE OF ORDERING INFORMATION



Notes:

- (1) All packages are RoHS-compliant (Lead-free, Halogen-free).
- (2) The standard lead finish is NiPdAu.
- (3) This device used in the above example is a CAT5113VI-10-GT3 (SOIC, Industrial Temperature, 10kΩ, NiPdAu, Tape & Reel).

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(4) For Matte-Tin finish, contact factory.

ORDERING PART NUMBER
CAT5113LI-01-G
CAT5113LI-10-G
CAT5113LI-50-G
CAT5113LI-00-G
CAT5113VI-01-G
CAT5113VI-10-G
CAT5113VI-50-G
CAT5113VI-00-G
CAT5113YI-01-G
CAT5113YI-10-G
CAT5113YI-50-G
CAT5113YI-00-G
CAT5113ZI-01-G
CAT5113ZI-10-G
CAT5113ZI-50-G
CAT5113ZI-00-G

REVISION HISTORY

Date	Rev.	Reason
10/09/2003	M	Revised Features Revised DC Electrical Characteristics
03/10/2004	N	Updated Potentiometer Parameters
03/29/2004	0	Changed Green Package marking for SOIC from W to V
04/02/2004	Р	Add 1kW version to data sheet
04/08/2004	Q	Eliminated data sheet designation Updated Tape and Reel specs in Ordering Information
01/25/2005	R	Updated Potentiometer Parameters
04/22/2006	S	Updated Example of Ordering Information
06/01/2007	Т	Added Package Outline Added MD- in front of Document No.

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